

<b>Notice of References Cited</b>	Application/Control No. 10/566,686		Applicant(s)/Patent Under Reexamination LIU ET AL.	
	Examiner JONATHAN C. LANGMAN		Art Unit 1794	Page 1 of 1

#### U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-2003/0235931	12-2003	Wada et al.	438/22
*	B	US-5,541,438	07-1996	Martin et al.	257/447
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
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	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

#### FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
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	T					

#### NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Winnerl et al. "Fast IR Si/SiGe superlattice MSM photodetectors with buried CoSi2 contacts", Microelectronic Engineering, Vol. 64, 2002, pgs 205-209.
	V	Winnerl et al. "MBE-growth of a Ge-CoSi2-Si heterostructures for vertical metal-semiconductor-metal photoconductors" , Microelectronic Engineering, Vol. 60, 2002, pgs 191-196.
	W	Gluck et al., "CoSi2 and TiSi2 for Si/SiGe heterodevices", Thin Solid Films, Vol. 270, 1995, pgs 549-554.
	X	Cheng et al. "Effects of Stress on the growth of TiSi2 thin films on (001)Si", Applied Physics Letters, Vol. 74, No. 10, 1999, pgs 1406-1408.

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.